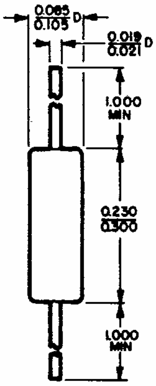
MICROWAVE DIODE CORPORATION

IN830
IN830A

SILICON UHF DETECTOR DIODE

The IN830 and IN830A are point contact barrier diodes used in signal detection. While Tangential Sensitivity is not specified in this instance, the diodes posess a minimum of -40 dbm up to 3 GHZ.



PACKAGE OUTLINE

Electrical Characteristics at T = 25°

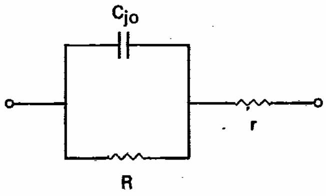
Burnout CW, 375 mw
Peak @ 1 us 15w
Typical .3pf C_{jo}

IN830 Detector rectification efficiency = 65% minimum at f = 100 mc

IN830A PIV = 5 volts minimum.

FIGURE 1

DIODE Equivalent Circuit



R = Series resistance
r = Spreading resistance
C_{jo} = Junction Capacitance

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